



Electrodeposited copper foil and process for making same

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This invention is directed to a controlled low profile electrodeposited copper foil. In one embodiment this foil has a substantially uniform randomly oriented grain structure that is essentially columnar grain free and twin boundary free and has an average grain size-of up to about 10 microns. In one embodiment this foil has an ultimate tensile strength measured at 23 DEG C in the range of about 87,000 to about 120,000 psi and an elongation measured at 180 DEG C of about 15% to about 28%. The invention is also directed to a process for making the foregoing foil, the process comprising: (A) flowing an electrolyte solution between an anode and a cathode and applying an effective amount of voltage across said anode and said cathode to deposit copper on said cathode; said electrolyte solution comprising copper ions, sulfate ions and at least one organic additive or derivative thereof, the chloride ion concentration of said solution being up to about 1 ppm; the current density being in the range of about 0.1 to about 5 A/cm<2>; and (B) removing copper foil from said cathode.

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(54) Electrodeposited copper foil and process for making same.

This invention is directed to a controlled low profile electrodeposited copper foil. In one embodiment this foil has a substantially uniform randomly oriented grain structure that is essentially columnar grain free and twin boundary free and has an average grain size-of up to about 10 microns. In one embodiment this foil has an ultimate tensile strength measured at 23°C in the range of about 87,000 to about 120,000 psi and an elongation measured at 180°C of about 15% to about 28%. The invention is also directed to a process for making the foregoing foil, the process comprising: (A) flowing an electrolyte solution between an anode and a cathode and applying an effective amount of voltage across said anode and said cathode to deposit copper on said cathode; said electrolyte solution comprising copper ions, sulfate ions and at least one organic additive or derivative thereof, the chloride ion concentration of said solution being up to about 1 ppm; the current density being in the range of about 0.1 to about 5 A/cm²; and (B) removing copper foil from said cathode.